

What is Claimed is:

5 1. An electroluminescent device having a plurality of pixels each with a first electrode stripe, an organic electroluminescent multilayer and a second electrode stripe, the device comprising:

a partition wall of an electrically insulating material projected from each of the first electrode stripes, the partition wall having a trapezoidal structure with the lower side wider than the upper side, wherein portions of the second electrode and possibly the organic luminescence multilayer formed on the partition wall are etched out, thereby any two adjacent pixels being electrically isolated.

10 2. A device as claimed in claim 1, wherein the partition wall is formed of a material selected from photoresist, silicon nitride and silicon oxide.

15 3. A device as claimed in claim 1, further comprising the first protective film formed only on each of the emitting pixels and the second protective film formed on the entire surface including on top of the first protective film.

20 4. A method for fabricating an electroluminescent device, comprising the steps of:
(1) forming a plurality of first electrode stripes at fixed intervals on a transparent substrate;

(2) forming an array of partition walls made of an electrically insulating material on the first electrode elements; having a trapezoidal structure with the lower side wider than the upper side:

(3) forming an organic electroluminescent multilayer, the second electrode layer, and the first protection layer in succession on the entire surface including on top of the partition walls;

(4) removing upper portions of films, unequivocally including the second electrode layer on top of the partition walls, whereby electrically isolating any two adjacent pixels; and

(5) forming the second protection layer on top of the etched-out surface.

5. A method as claimed in claim 4, wherein the first protective coating is formed by a method selected from spin-coating and Dr. Blade method.

6. A method as claimed in claim 4, wherein the partition wall is formed of a material selected from photoresist, silicon nitride and silicon oxide.

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